

# isc N-Channel MOSFET Transistor IPD60R1K4C6,IIPD60R1K4C6

## FEATURES

- Static drain-source on-resistance: R<sub>DS</sub>(on)≤1.4Ω
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## DESCRITION

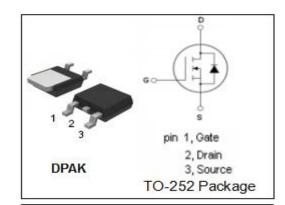
· Fast switching

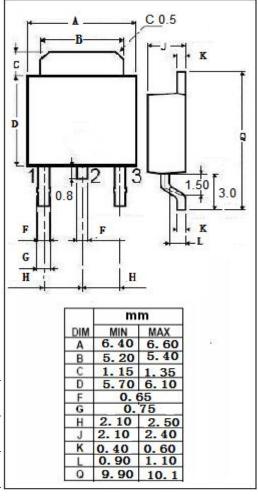
# • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                               | VALUE                                       | UNIT         |  |
|------------------|---|---|--------------|--|
| V <sub>DSS</sub> | Drain-Source Voltage                    | 600   | V            |  |
| V <sub>GS</sub>  | Gate-Source Voltage                     | ±20   | V            |  |
| I <sub>D</sub>   | Drain Current-Continuous                | 3.2   | Α            |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed             | 8   | А            |  |
| P <sub>D</sub>   | Total Dissipation @T <sub>C</sub> =25°C | otal Dissipation @T <sub>C</sub> =25°C 28.4 |              |  |
| Tj               | Max. Operating Junction Temperature 150 |   | $^{\circ}$ C |  |
| T <sub>stg</sub> | Storage Temperature                     | -55~150                                     | $^{\circ}$   |  |

## THERMAL CHARACTERISTICS

| SYMBOL   | PARAMETER                             | MAX | UNIT |
|----------|---------------------------------------|-----|------|
| Rth(j-c) | Channel-to-case thermal resistance    | 4.4 | °C/W |
| Rth(j-a) | Channel-to-ambient thermal resistance | 62  | °C/W |







# isc N-Channel MOSFET Transistor

# IPD60R1K4C6,IIPD60R1K4C6

## **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS                                  | MIN | ТҮР | MAX | UNIT |
|---------------------|--------------------------------|---|-----|-----|-----|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA | 600 |     |     | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | VDS=VGS; I <sub>D</sub> =0.09mA             | 2.5 |     | 3.5 | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =1.1A  |     |     | 1.4 | Ω    |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> =20V; V <sub>DS</sub> =0V   |     |     | 0.1 | μА   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V |     |     | 1   | μА   |
| $V_{SD}$            | Diode forward voltage          | I <sub>F</sub> =1.4A, V <sub>GS</sub> = 0V  |     | 0.9 |     | V    |

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